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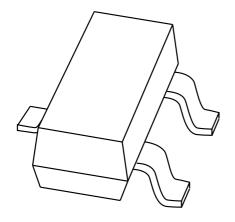
If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

### **DISCRETE SEMICONDUCTORS**

## DATA SHEET



**PBSS5250T** 50 V, 2 A PNP low  $V_{CEsat}$  (BISS) transistor

Product data sheet 2003 Oct 09



### 50 V, 2 A PNP low V<sub>CEsat</sub> (BISS) transistor

#### PBSS5250T

#### **FEATURES**

- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability: I<sub>C</sub> and I<sub>CM</sub>
- Higher efficiency leading to less heat generation
- Reduced printed-circuit board requirements
- Cost effective alternative to MOSFETs in specific applications.

#### **APPLICATIONS**

- Power management
  - DC/DC converters
  - Supply line switching
  - Battery charger
  - LCD backlighting
- Peripheral drivers
  - Driver in low supply voltage applications (e.g. lamps and LEDs)
  - Inductive load driver (e.g. relays, buzzers and motors).

#### **DESCRIPTION**

PNP BISS transistor in a SOT23 plastic package offering ultra low  $V_{\text{CEsat}}$  and  $R_{\text{CEsat}}$  parameters.

#### **MARKING**

TYPE NUMBER	MARKING CODE(1)
PBSS5250T	3H*

#### Note

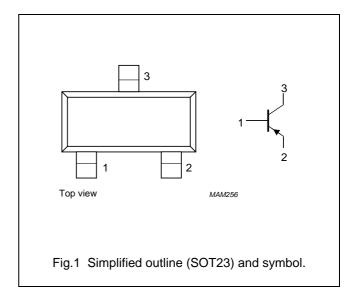
- 1. \* = p: Made in Hong Kong.
  - \* = t: Made in Malaysia.
  - \* = W: Made in China.

#### **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	MAX.	UNIT
V <sub>CEO</sub>	collector-emitter voltage	-50	V
I <sub>C</sub>	collector current (DC)	-2	Α
I <sub>CM</sub>	I <sub>CM</sub> peak collector current		Α
R <sub>CEsat</sub>	equivalent on-resistance		mΩ

#### **PINNING**

PIN	DESCRIPTION	
1	base	
2	emitter	
3	collector	



#### **ORDERING INFORMATION**

TYPE NUMBER		PACKAGE			
TIPE NOWIBER	NAME DESCRIPTION VERSION				
PBSS5250T	_	plastic surface mounted package; 3 leads	SOT23		

## 50 V, 2 A PNP low $V_{CEsat}$ (BISS) transistor

PBSS5250T

#### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	_	-50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	_	-50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	_	-5	V
I <sub>C</sub>	collector current (DC)		_	-2	Α
I <sub>CM</sub>	peak collector current	single peak	_	-3	Α
I <sub>B</sub>	base current (DC)		_	-300	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1		300	mW
		T <sub>amb</sub> ≤ 25 °C; note 2	_	480	mW
Tj	junction temperature		_	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

#### **Notes**

- 1. Device mounted on a FR4 printed-circuit board; single-sided copper; tinplated; standard footprint.
- 2. Device mounted on a FR4 printed-circuit board; single-sided copper; tinplated; mounting pad for collector 1 cm<sup>2</sup>.

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	in free air; note 1	417	K/W
		in free air; note 2	260	K/W

#### Notes

- 1. Device mounted on a FR4 printed-circuit board; single-sided copper; tinplated; standard footprint.
- 2. Device mounted on a FR4 printed-circuit board; single-sided copper; tinplated; mounting pad for collector 1 cm<sup>2</sup>.

# 50 V, 2 A PNP low $V_{CEsat}$ (BISS) transistor

PBSS5250T

#### **CHARACTERISTICS**

 $T_j$  = 25 °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>CBO</sub>	collector cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0$	_	_	-100	nA
		V <sub>CB</sub> = −50 V; I <sub>E</sub> = 0; T <sub>j</sub> = 150 °C	_	_	-50	μΑ
I <sub>EBO</sub>	emitter cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0$	_	_	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = -2 \text{ V}; I_{C} = 0.5 \text{ A}$	200	-	-	
		$V_{CE} = -2 \text{ V; } I_{C} = 1 \text{ A; note 1}$	200	_	-	
		$V_{CE} = -2 \text{ V}; I_{C} = 2 \text{ A}; \text{ note 1}$	130	_	-	
V <sub>CEsat</sub>	collector-emitter saturation	$I_C = -0.5 \text{ A}; I_B = -50 \text{ mA}$	_	_	-90	mV
	voltage	$I_C = -1 \text{ A}; I_B = -50 \text{ mA}$	_	_	-180	mV
		$I_C = -2 \text{ A}; I_B = -100 \text{ mA}$	_	_	-300	mV
R <sub>CEsat</sub>	equivalent on-resistance	$I_C = -2 \text{ A}$ ; $I_B = -200 \text{ mA}$ ; note 1	_	_	150	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C = -2 \text{ A}$ ; $I_B = -100 \text{ mA}$ ; note 1	_	_	-1.1	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE} = -2 \text{ V}; I_{C} = -1 \text{ A}; \text{ note 1}$	-1.2	_	-	V
f <sub>T</sub>	transition frequency	$I_C = -100 \text{ mA}; V_{CE} = -5 \text{ V};$ f = 100 MHz	100	_	_	MHz
C <sub>c</sub>	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = I_e = 0; f = 1 \text{ MHz}$	_	_	35	pF

#### Note

1. Pulse test:  $t_p \leq 300~\mu s;~\delta \leq 0.02.$ 

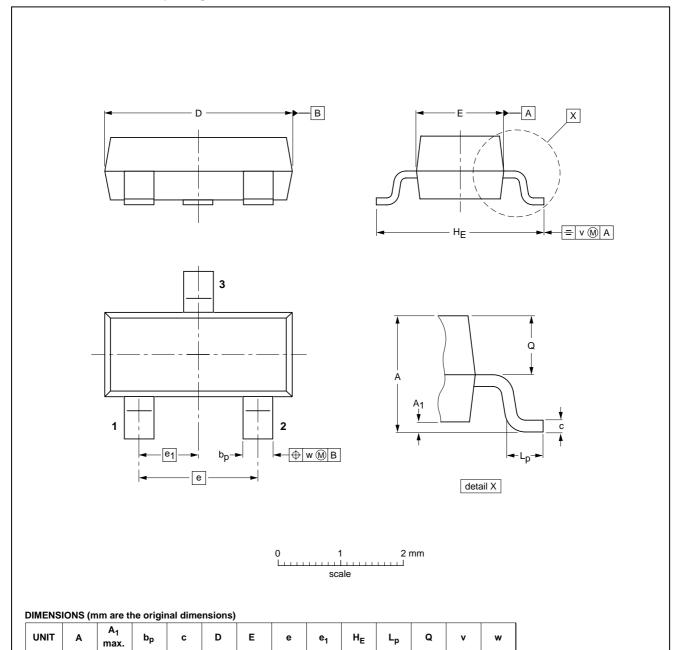
50 V, 2 A PNP low  $V_{CEsat}$  (BISS) transistor

PBSS5250T

#### **PACKAGE OUTLINE**

Plastic surface mounted package; 3 leads

SOT23



OUTLINE		REFERENCES			EUROPEAN	ISSUE DATE	
VEF	RSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
S	OT23		TO-236AB				<del>97-02-28</del> 99-09-13

0.95

0.45

0.15

0.55

0.45

0.1

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0.48

0.38

0.1

mm

0.15

0.09

3.0

2.8

1.4

1.9

### 50 V, 2 A PNP low V<sub>CEsat</sub> (BISS) transistor

PBSS5250T

#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

#### **Notes**

- 1. Please consult the most recently issued document before initiating or completing a design.
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#### **Customer notification**

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#### **Contact information**

For additional information please visit: http://www.nxp.com

For sales offices addresses send e-mail to: salesaddresses@nxp.com

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